

2SK1338

Silicon N Channel MOS FET

REJ03G0935-0200
(Previous: ADE-208-1275)
Rev.2.00
Sep 07, 2005

Application

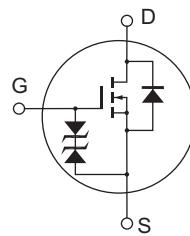
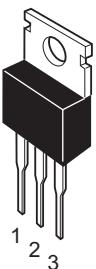
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

RENESAS Package code: PRSS0004AC-A
(Package name: TO-220AB)



1. Gate
2. Drain
(Flange)
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	900	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	2	A
Drain peak current	I _{D(pulse)} ^{*1}	6	A
Body to drain diode reverse drain current	I _{DR}	2	A
Channel dissipation	P _{ch} ^{*2}	50	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

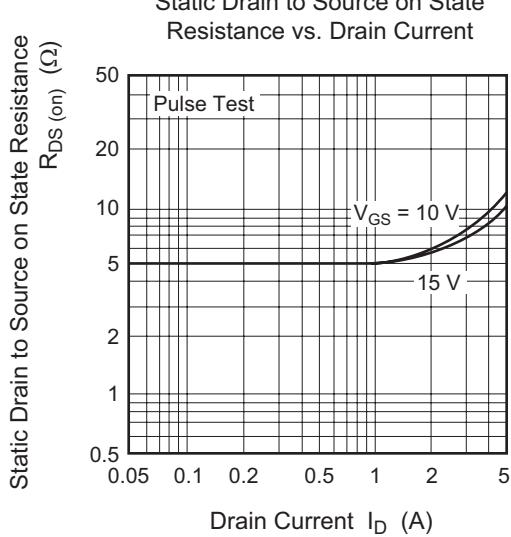
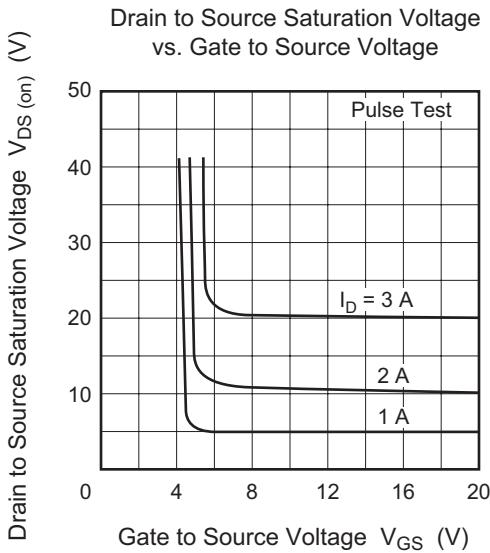
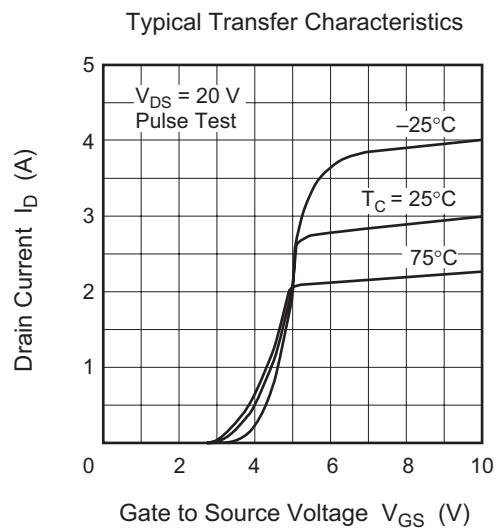
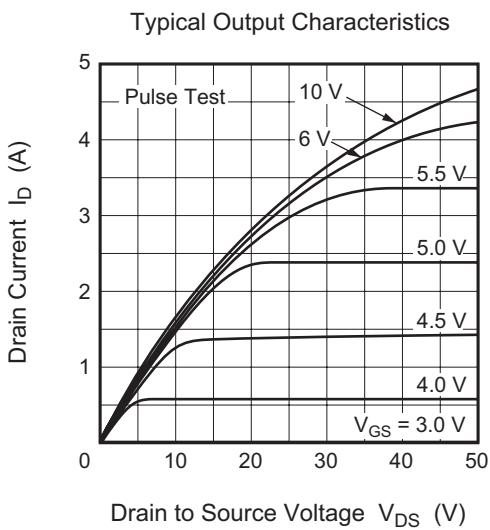
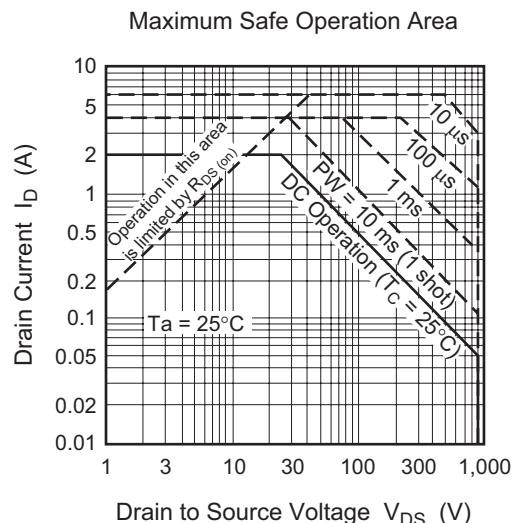
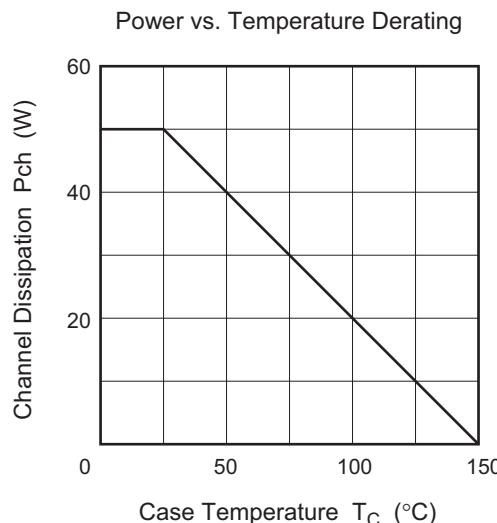
2. Value at T_C = 25°C**Electrical Characteristics**

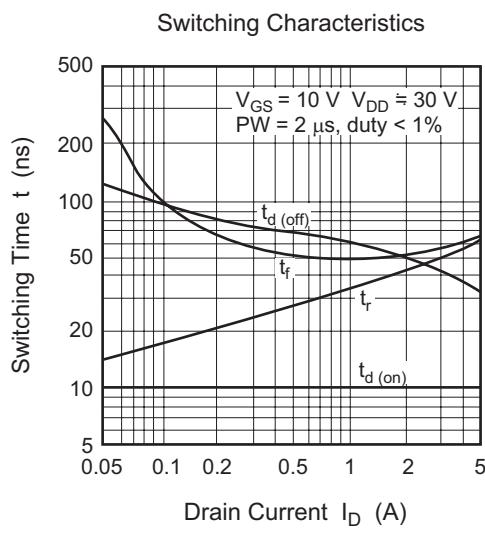
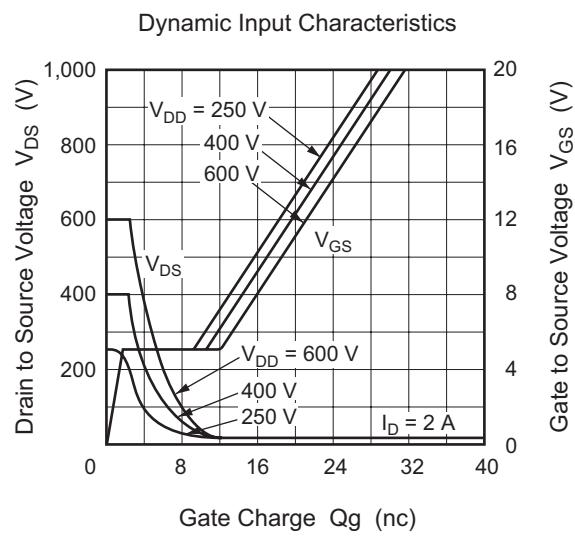
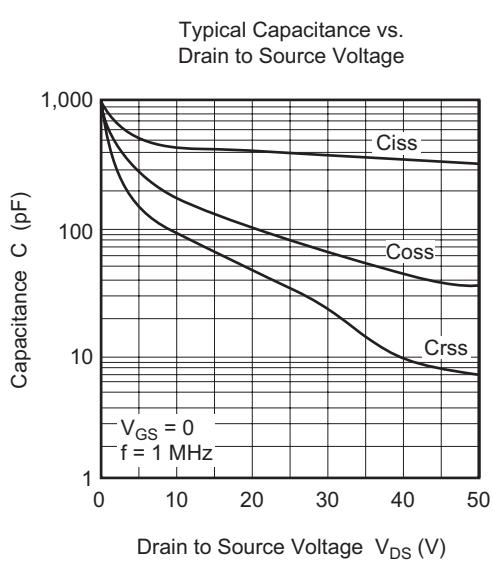
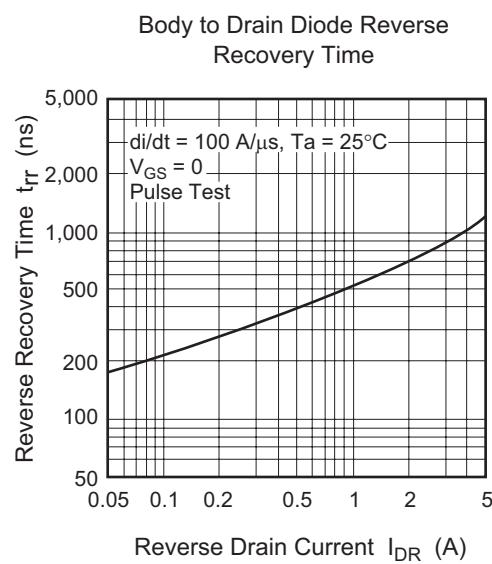
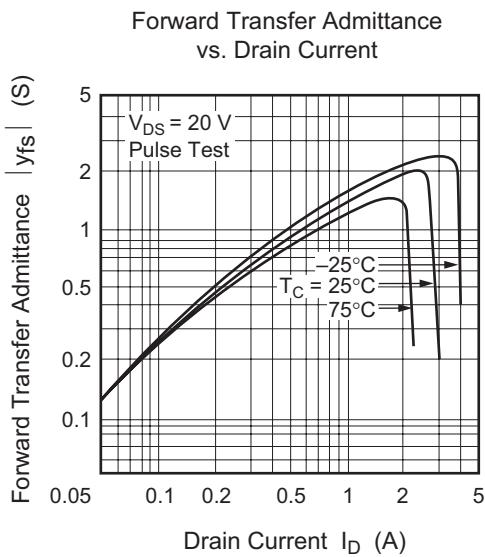
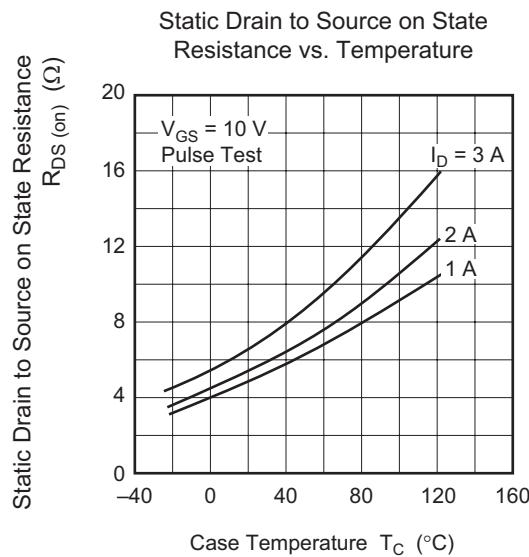
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to Source breakdown voltage	V _{(BR)DSS}	900	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to Source breakdown voltage	V _{(BR)GSS}	±30	—	—	V	I _G = ±100 μA, V _{DS} = 0
Gate to Source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±25 V, V _{DS} = 0
Zero Gate voltage Drain current	I _{DSS}	—	—	250	μA	V _{DS} = 720 V, V _{GS} = 0
Gate to Source cutoff voltage	V _{GS(off)}	2.0	—	3.0	V	I _D = 1 mA, V _{DS} = 10 V
Static Drain to Source on state resistance	R _{DS(on)}	—	5.0	7.0	Ω	I _D = 1 A, V _{GS} = 10 V ^{*3}
Forward transfer admittance	y _{fs}	0.9	1.5	—	S	I _D = 1 A, V _{DS} = 20 V ^{*3}
Input capacitance	C _{iss}	—	425	—	pF	V _{DS} = 10 V, V _{GS} = 0,
Output capacitance	C _{oss}	—	175	—	pF	f = 1 MHz
Reverse transfer capacitance	C _{rss}	—	85	—	pF	
Turn-on delay time	t _{d(on)}	—	10	—	ns	I _D = 1 A, V _{GS} = 10 V,
Rise time	t _r	—	35	—	ns	R _L = 30 Ω
Turn-off delay time	t _{d(off)}	—	60	—	ns	
Fall time	t _f	—	50	—	ns	
Body to Drain diode forward voltage	V _{DF}	—	0.9	—	V	I _F = 2 A, V _{GS} = 0
Body to Drain diode reverse recovery time	t _{rr}	—	700	—	ns	I _F = 2 A, V _{GS} = 0, di _F /dt = 100 A/μs

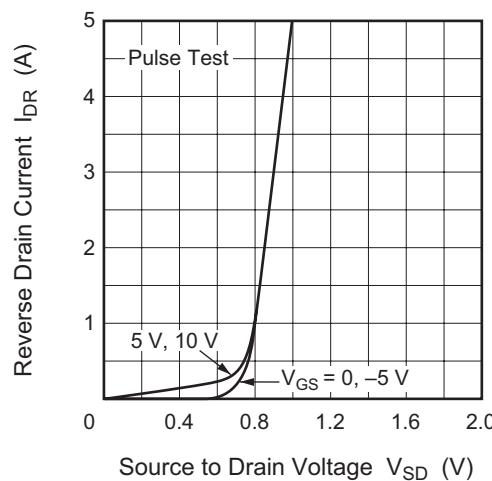
Note: 3. Pulse test

Main Characteristics

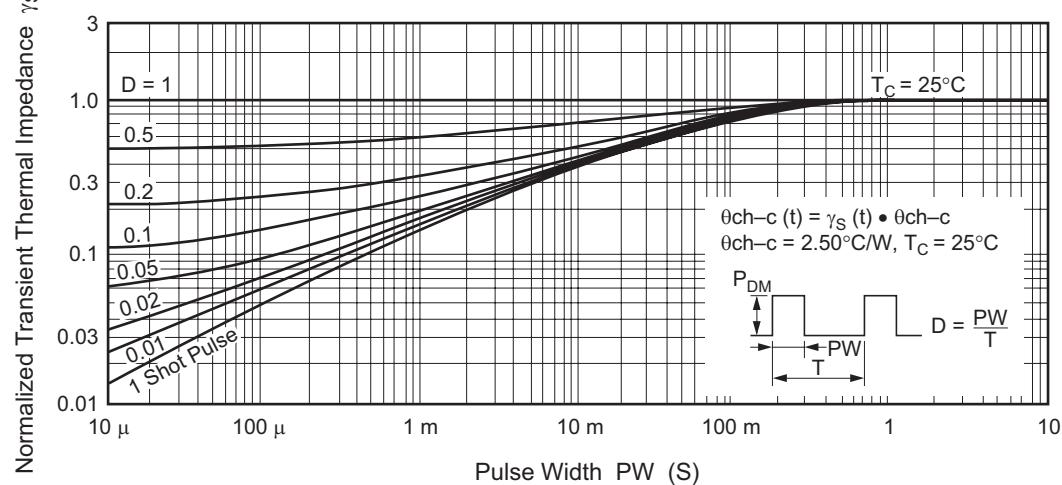




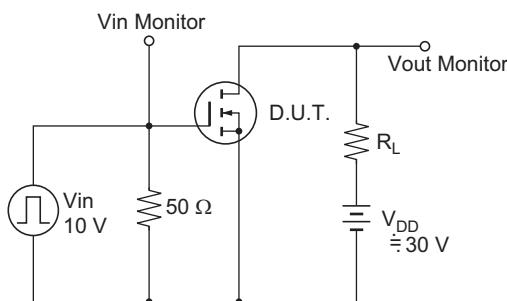
Reverse Drain Current vs.
Source to Drain Voltage



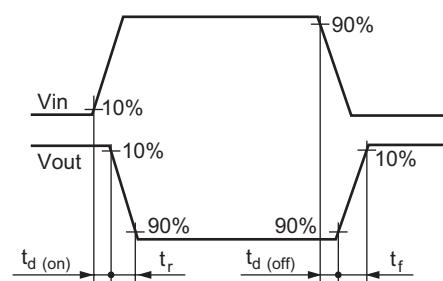
Normalized Transient Thermal Impedance vs. Pulse Width



Switching Time Test Circuit

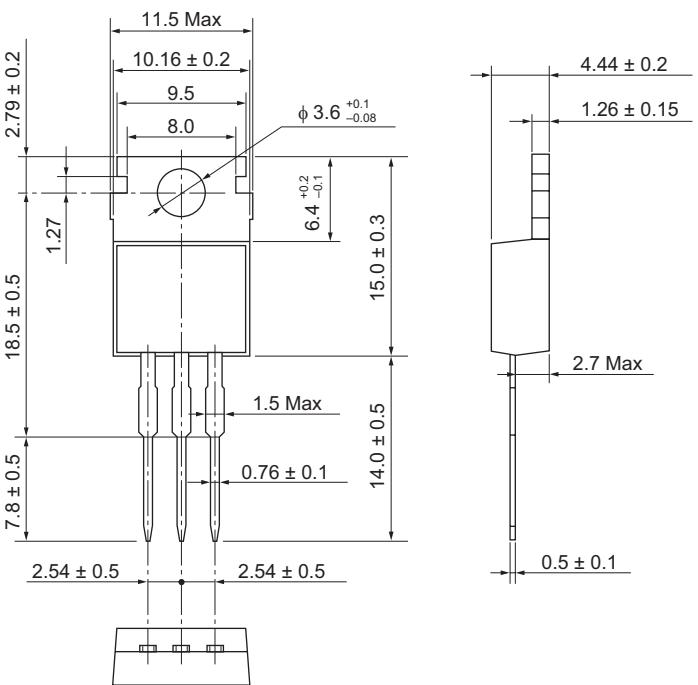


Waveforms



Package Dimensions

JEITA Package Code	RENESAS Code	Package Name	MASS[Typ.]	Unit: mm
SC-46	PRSS0004AC-A	TO-220AB / TO-220ABV	1.8g	



Technical drawing of the 2SK1338 package showing top and side views with dimension lines. Top view shows lead spacing, lead height, body width, and lead thickness. Side view shows total height, lead thickness, and lead pitch.

Ordering Information

Part Name	Quantity	Shipping Container
2SK1338-E	500 pcs	Box (Sack)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

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Renesas Technology Taiwan Co., Ltd.
10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.
Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.
Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510